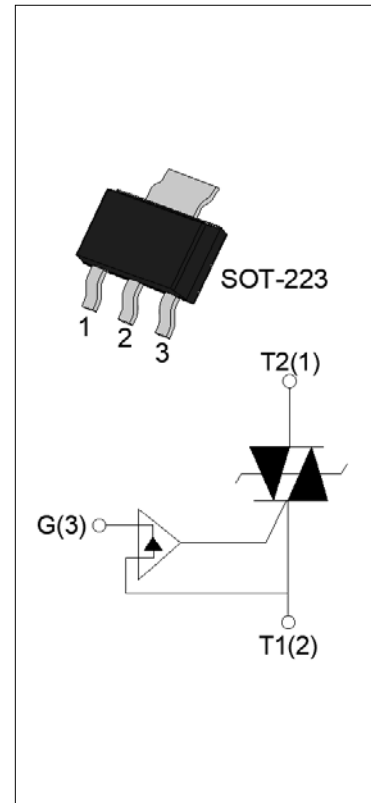




ACJP01V-800SW 1A TRIAC

Rev.A.1.0

The ACJP01V-800SW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. The ACJP01V-800SW embeds a TVS structure to absorb the inductive turn-off energy such as those described in the IEC 61000-4-5 standards. At the same time, the triac shields the positive signal trigger to reduce the probability of product misoperation. It is triggered with a negative gate current flowing out of the gate pin. Package SOT-223 is RoHS compliant.



Symbol	Value	Unit
$I_{T(RMS)}$	1	A
V_{DRM}/V_{RRM}	800	V
$I_{GT\ II/III}$	10/10	mA

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	800	V
RMS on-state current ($T_c \leq 93^\circ\text{C}$)	$I_{T(RMS)}$	1	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	18	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		19.8	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	1.62	A^2s
Critical rate of rise of on-state current ($I_G=2 I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	di/dt	100	$\text{A}/\mu\text{s}$
Peak gate current ($t_p=20\mu\text{s}$, $T_j=125^\circ\text{C}$)	I_{GM}	1	A
Positive applied gate voltage	V_{GM}	15	V

Average gate power dissipation ($T_j=125^\circ\text{C}$)	$P_{G(AV)}$	0.1	W
Peak gate power	P_{GM}	2	W
Peak pulse voltage ($T_j=25^\circ\text{C}$; non-repetitive, off-state; FIG.8)	V_{pp}	4.5	kV

(T_j=25°C unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V R_L=33$	II-III	MAX.	10	mA
V_{GT}		II-III	MAX.	1.3	V
V_{GD}	$V_D=V_{DRM} T_j=125^\circ\text{C}$ $R_L=3.3K$	II-III	MIN.	0.15	V
I_L	$I_G=1.2I_{GT}$	II	MAX.	25	mA
		III		10	
I_H	$I_T=100\text{mA}$		MAX.	10	mA
dV/dt	$V_D=540V$ Gate Open $T_j=125^\circ\text{C}$		MIN.	100	V/ μs
(dI/dt) _c	(dV/dt) _c =10V/ μs , $T_j=125^\circ\text{C}$		MIN.	0.6	A/ms
t_{on}	$I_G=20\text{mA} I_A=200\text{mA} I_R=20\text{mA}$ $T_j=25^\circ\text{C}$		TYP.	2.5	μs
t_{off}				25	
V_{CL}	$I_{CL}=0.1\text{mA} t_p=1\text{ms}$		MIN.	900	V

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=1.1A t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.3	V
V_{TO}	Threshold voltage	$T_j=125^\circ\text{C}$	0.77	V
R_D	Dynamic resistance	$T_j=125^\circ\text{C}$	276	m
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	μA
I_{RRM}		$T_j=125^\circ\text{C}$	0.4	mA

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	25	$^\circ\text{C/W}$
$R_{th(j-a)}$	junction to ambient (AC)	150	$^\circ\text{C/W}$

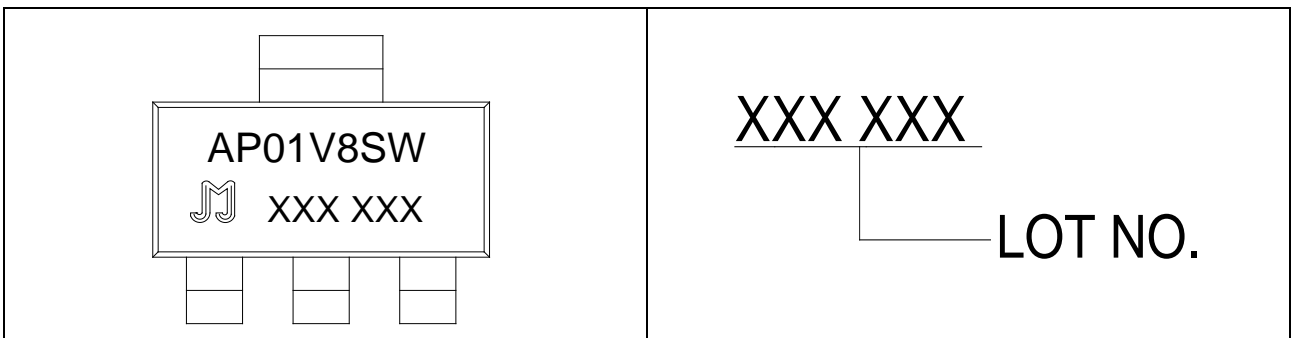
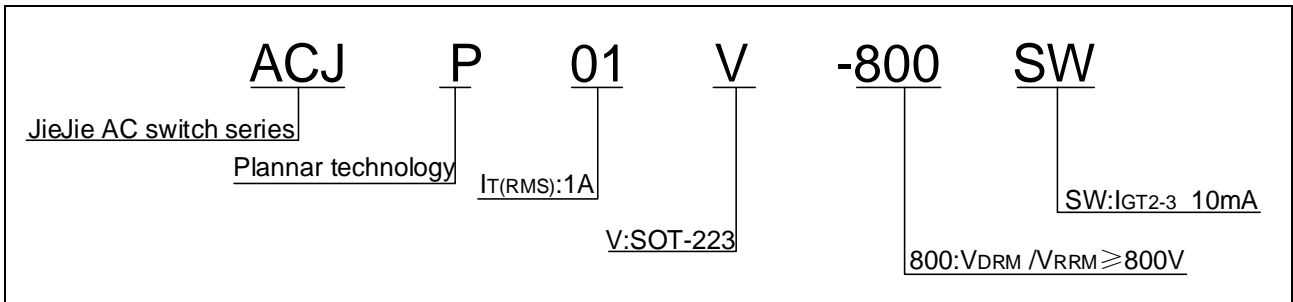


FIG.1 Maximum power dissipation versus RMS on-state current

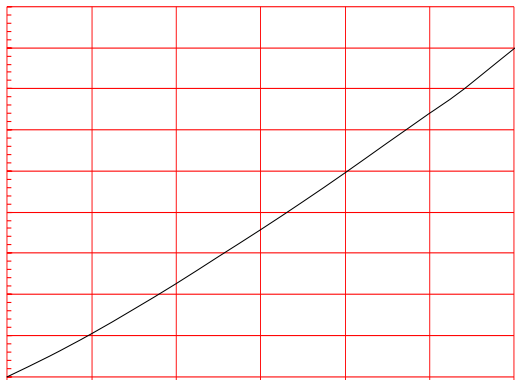


FIG.2: RMS on-state current versus case temperature

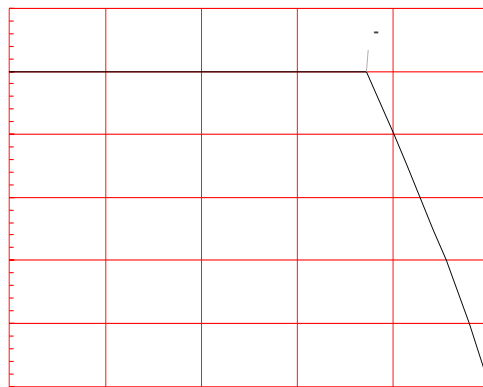


FIG.3: RMS on-state current versus ambient temperature (printed circuit board FR4,copper thickness:35μm)(full cycle)

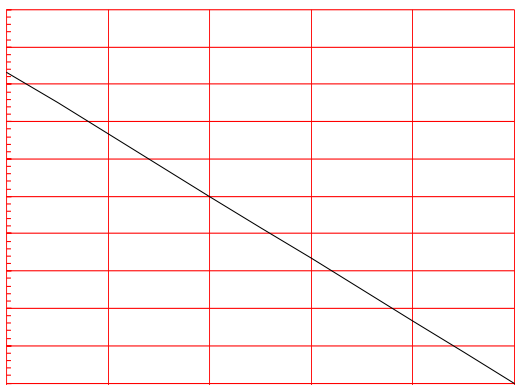


FIG.4: Surge peak on-state current versus number of cycles

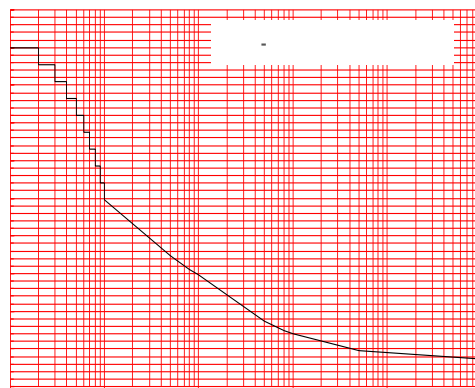


FIG.5: On-state characteristics

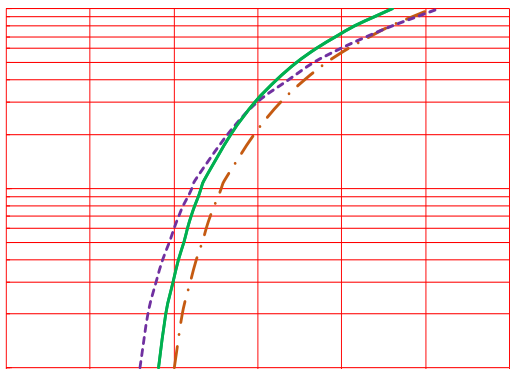


FIG.6: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($di/dt < 100\text{A}/\mu\text{s}$)

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

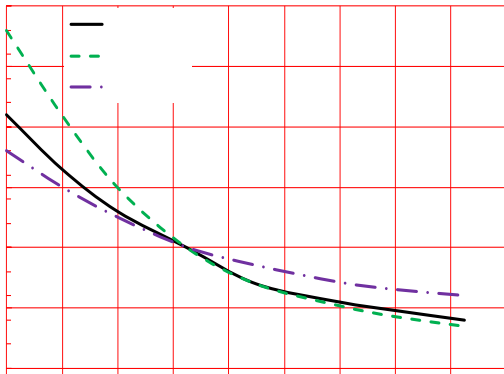
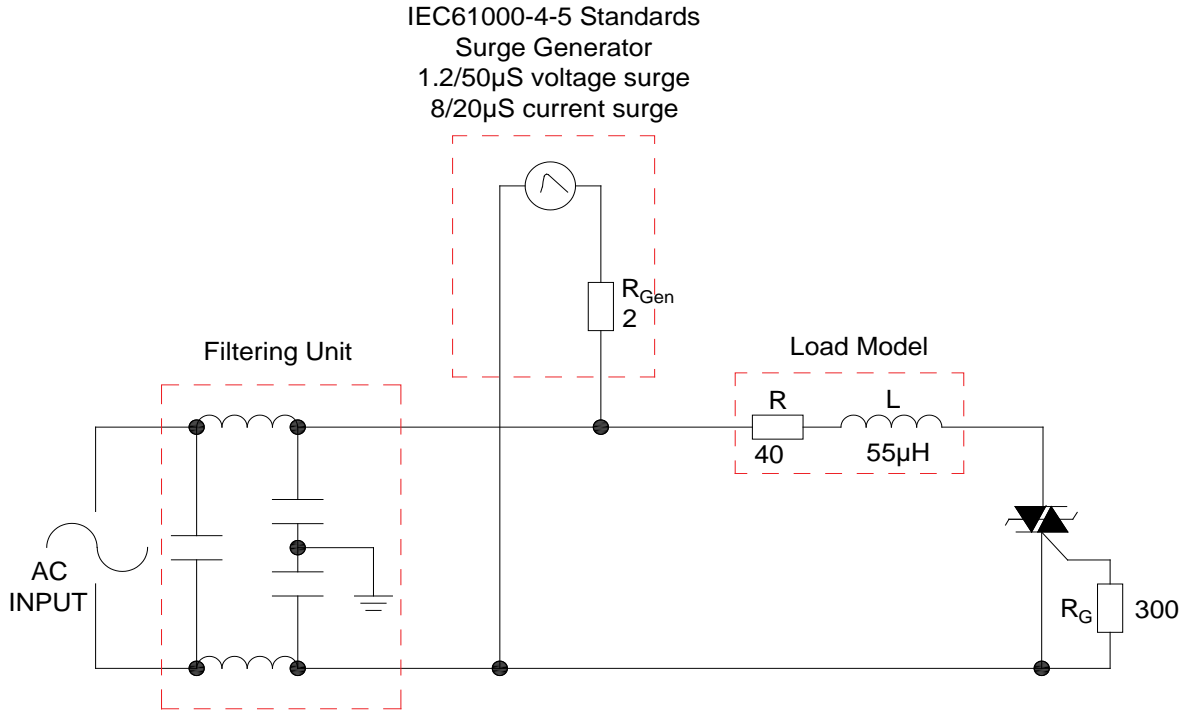
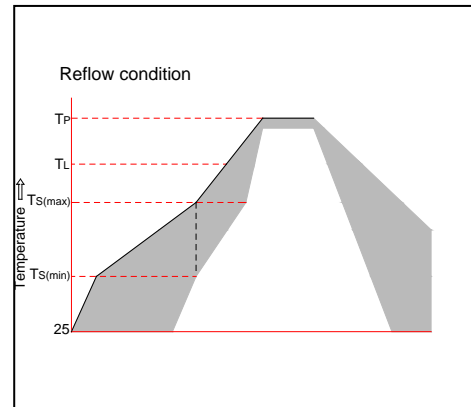


FIG.8: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



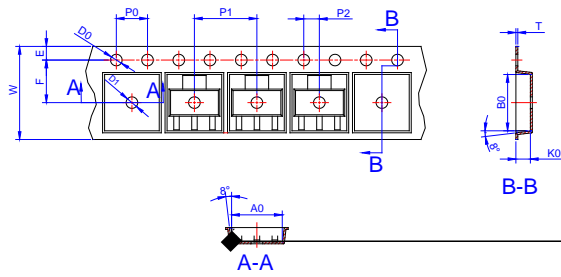
Reflow Condition		Pb-Free assembly (see figure at right)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150 $^{\circ}$ C
	-Temperature Max($T_{s(max)}$)	+200 $^{\circ}$ C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquidus Temp (T_L) to peak)		3 $^{\circ}$ C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3 $^{\circ}$ C/sec. Max
Reflow	-Temperature(T_L)(Liquidus)	+217 $^{\circ}$ C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5) $^{\circ}$ C
Time within 5 $^{\circ}$ C of actual Peak Temp (t_p)		20-40secs.
Ramp-down Rate		6 $^{\circ}$ C/sec. Max
Time 25 $^{\circ}$ C to Peak Temp (T_p)		8 min. Max
Do not exceed		+260 $^{\circ}$ C



Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
ACJP01V-800SW	800	10	SOT-223	4,000	Tape & Reel

Document Revision History


Date	Revision	Changes
Apr.10, 2023	A.1.0	Last updated



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	-		12.30	-		0.482
E	1.65	1.75	1.85	0.065	0.069	0.073
F	5.45	5.50	5.55	0.215	0.217	0.219
D0		1.55	1.60		0.061	0.063
D1		-	-			
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.95	2.00	2.05	0.077	0.079	0.081
10P0	39.80	40.00	40.20	1.567	1.575	1.583
A0	6.85	6.95	7.05	0.269	0.273	0.276
B0	7.15	7.25	7.35	0.280	0.284	0.288
K0	1.95	2.05	2.15	0.076	0.080	0.084
T	0.20	0.25	0.30	0.008	0.010	0.012

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